

10/594391

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

**IAP5 Rec'd PCT/PTO 27 SEP 2006**

**MOSELUND ET AL**

Atty. Ref.: 2590-169

Serial No. **Unknown**

Group:

National Phase of: **PCT/IB2005/051049**

International Filing Date: **29 March 2005**

Filed: **Herewith**

Examiner:

For: **LIGHT PHASE MODULATOR**

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September 27, 2006

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**INFORMATION DISCLOSURE STATEMENT**

Sir:

As suggested by 37 C.F.R. 1.97, the undersigned attorney brings to the attention of the Patent and Trademark Office the references listed on the attached form PTO/SB/08a. Copies of the non-U.S. references are enclosed. This is not to be construed as a representation that a search has been made or that no better prior art exists, or that a reference is relevant merely because cited. A copy of the International Search Report, as well as the Written Opinion, are also enclosed.

The Examiner is requested to initial the attached form PTO/SB/08a and to return a copy of the initialed document to the undersigned as an indication that the attached references have been considered and made of record.

Respectfully submitted,

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By:



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Sheet 1 of 1

## INFORMATION DISCLOSURE CITATION

ATTY. DOCKET NO.

SERIAL NO.

2590-169

Unknown

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APPLICANT

MOSELUND ET AL

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(Use several sheets if necessary)

FILING DATE

GROUP

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## U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
/V.P./	6,298,177	10/2001	House			

## FOREIGN PATENT DOCUMENTS

DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
					YES	NO
/V.P./	WO 03/044590 A1	5/2003				

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	International Search Report mailed September 14, 2005 in PCT/IB2005/051049.
	Written Opinion mailed September 14, 2005 in PCT/IB2005/051049.

*Examiner	/Vipin Patel/	Date Considered	03/30/2008
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Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.